Change ROM contents... while enjoying MOS cost savings

The addition of our new MOS READ-Only Memory Systems lets you achieve both field programmability and low MOS costs. How? Easy. Design with our standard SBS braid system (200 nsec access/500 nsec cycle time); when you're sure you've made your last content change, go into volume production with our MOS systems. You won't end up paying several masking charges because you made repeated content changes.

How easy? Plug out and plug in. They're pin for pin compatible. Same mechanical form factor. A design approach that's based on over 5,000 systems in the field. Let us tell you the whole story about our MRM Model MOS memory systems. Write Memory Technology, Inc., 83 Boston Post Road, Sudbury, Massachusetts 01776.